150V N-Channel MOSFETs

PDN02N15

General Description

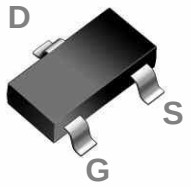
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

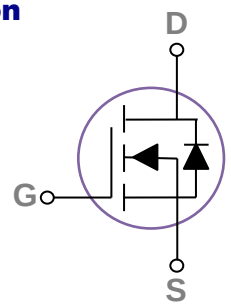
BVDSS	RDSON	ID
150V	480mΩ	1.2A

Features

- *150V,1.2A, RDS(ON) =480mΩ@VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*

SOT23-3 Pin Configuration





Applications

- *Networking*
- *Load Switch*
- *LED applications*

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_A=25℃)	1.2	A
	Drain Current – Continuous (T_A=70℃)	0.96	A
I_{DM}	Drain Current – Pulsed[1]	4.8	A
P_D	Power Dissipation (T_A=25℃)	1.56	W
	Power Dissipation – Derate above 25℃	0.012	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	150	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=150V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=120V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=1A	---	380	480	mΩ
		V_{GS}=6V , I_D=0.5A	---	410	520	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	3	4	V
gfs	Forward Transconductance	V_{DS}=10V , I_D=1A	---	1.7	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=75V , V_{GS}=10V , I_D=1A	---	8.1	16	nC
Q_{gs}	Gate-Source Charge[2,3]		---	2	4	
Q_{gd}	Gate-Drain Charge[2,3]		---	2.7	5.4	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DD}=75V , V_{GS}=10V , R_G=10Ω , I_D=1A	---	8.2	16	ns
T_r	Rise Time[2,3]		---	5.8	12	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	14.8	28	
T_f	Fall Time[2,3]		---	8	16	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	350	700	pF
C_{oss}	Output Capacitance		---	34	68	
C_{rss}	Reverse Transfer Capacitance		---	26	52	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	2	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	1.2	A
I_{SM}	Pulsed Source Current		---	---	2.4	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	V_{GS}=0V,I_S=1A , di/dt=100A/μs , T_J=25℃	---	43	---	ns
Q_{rr}	Reverse Recovery Charge		---	37	---	nC

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

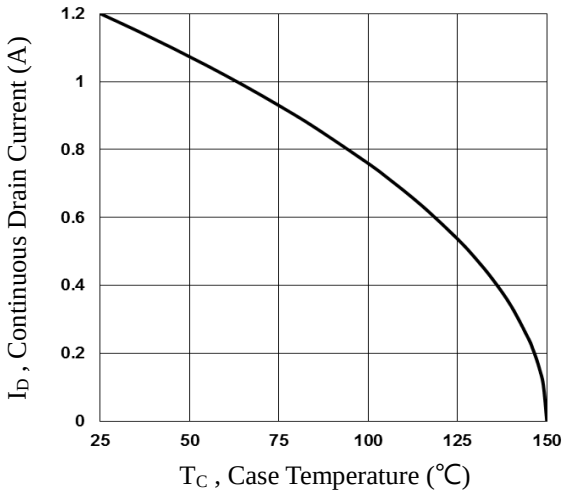


Fig.1 Continuous Drain Current vs. T_C

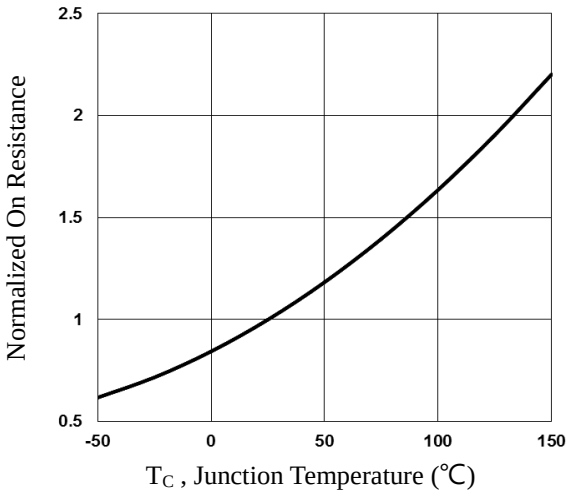


Fig.2 Continuous Drain Current vs. T_C

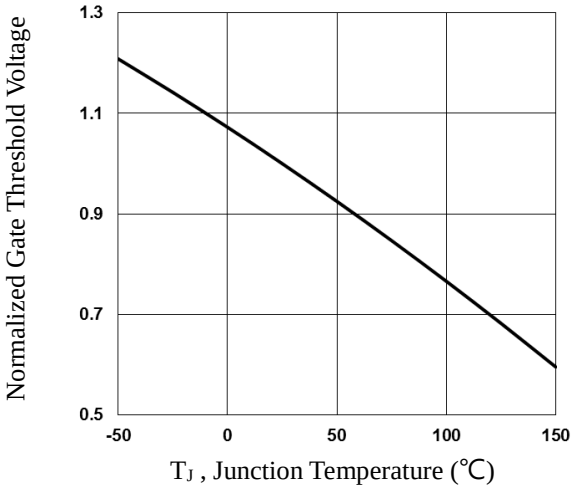


Fig.3 Normalized V_{th} vs. T_J

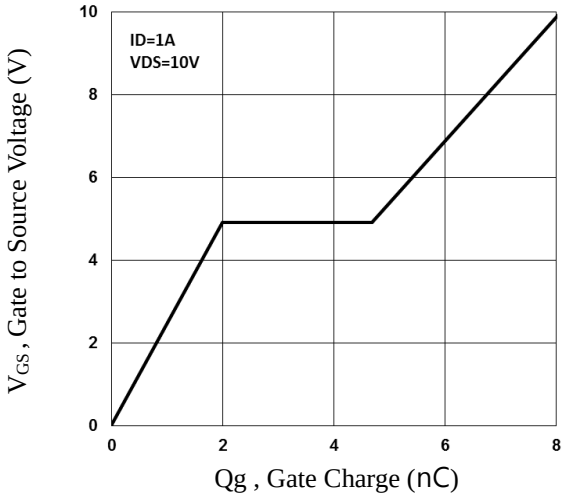


Fig.4 Gate Charge Waveform

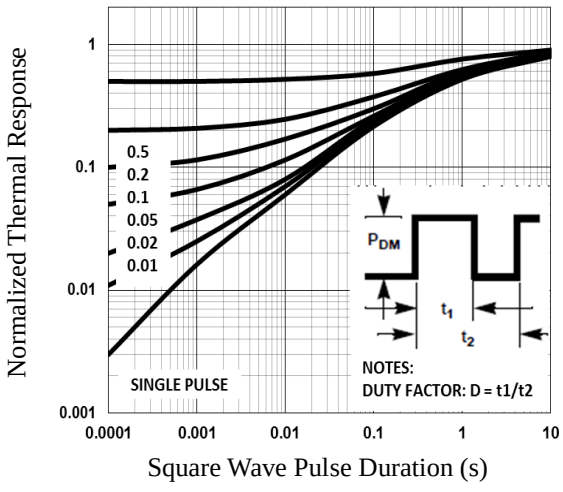


Fig.5 Normalized Transient Impedance

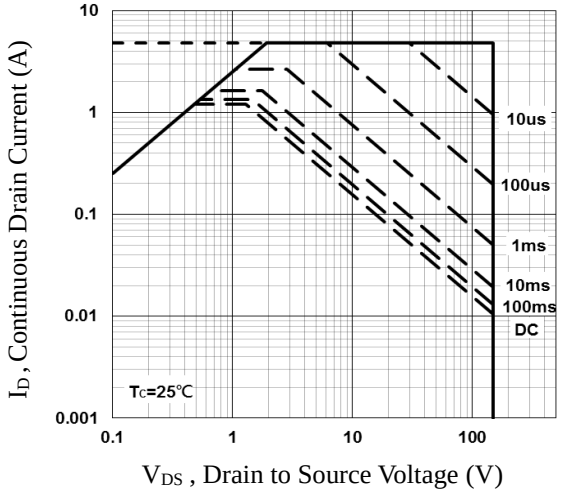


Fig.6 Maximum Safe Operation Area

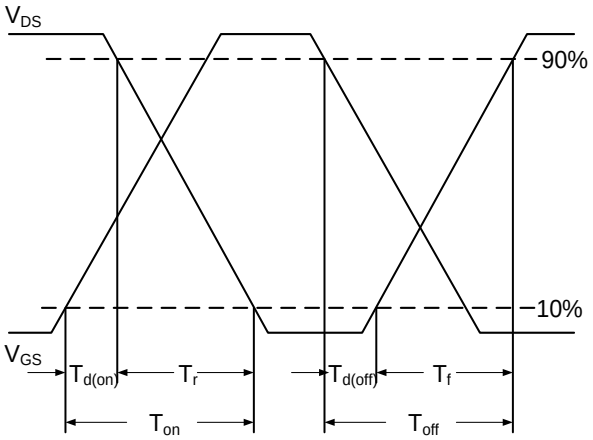


Fig.7 Switching Time Waveform

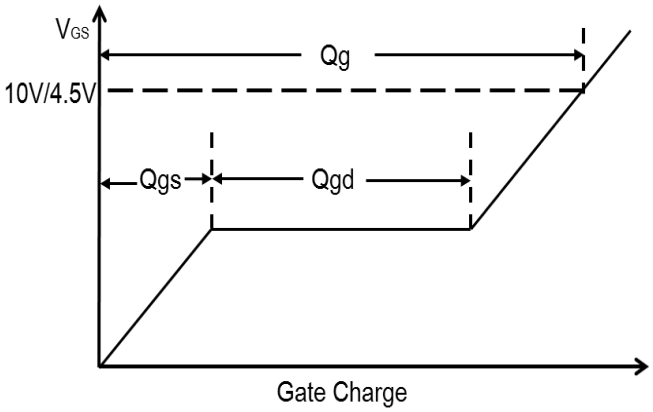
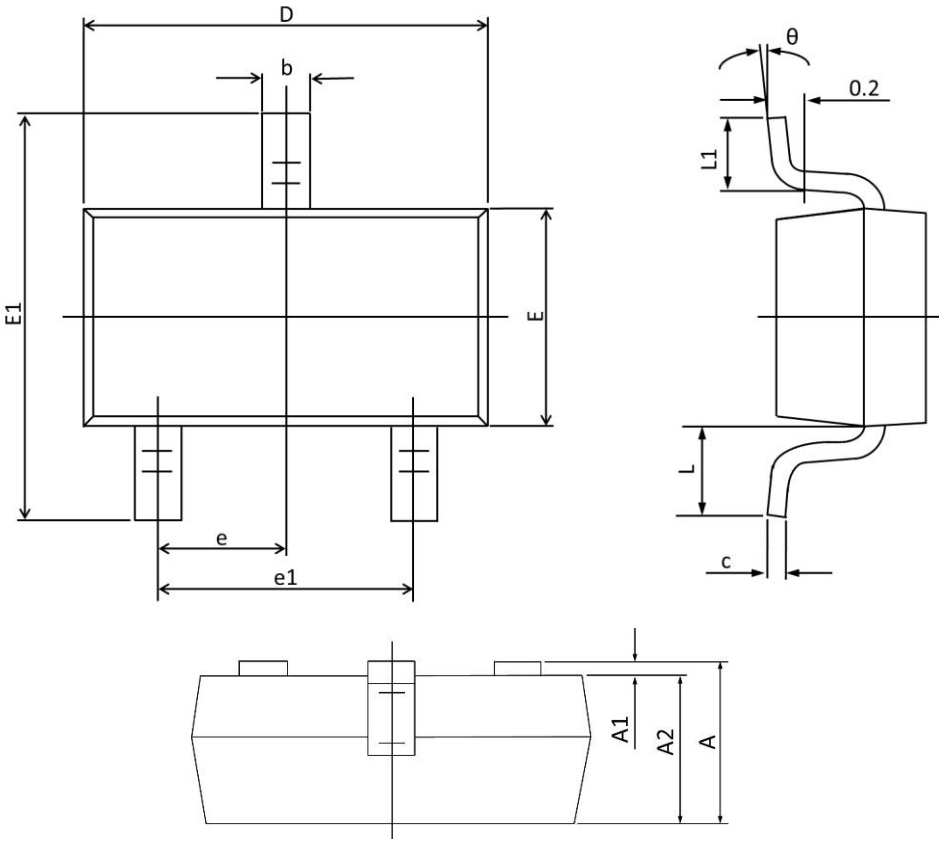


Fig.8 Gate Charge Waveform

SOT23-3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.450	0.041	0.057
A1	---	0.150	---	0.006
A2	0.900	1.300	0.035	0.051
b	0.300	0.490	0.012	0.019
c	0.100	0.200	0.004	0.008
D	2.820	3.050	0.111	0.120
E	1.500	1.750	0.059	0.069
E1	2.600	3.000	0.102	0.118
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.700 REF.		0.028 REF.	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°